

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

TK8P65W

• FEATURES

- Drain Current I_D = 7.8A@ T_C=25°C
- Drain Source Voltage-
 - : V_{DSS}= 650V(Min)
- Static Drain-Source On-Resistance
- : R_{DS(on)} = 0.67 Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

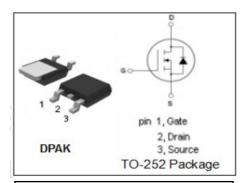
APPLICATIONS

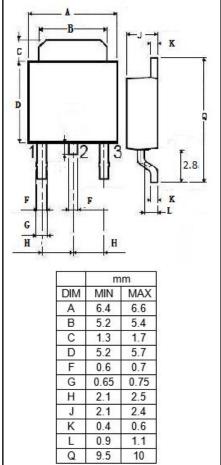
Switching power supplies, converters, AC and DC motor controls

ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL PARAMETER VALUE UNIT Drain-Source Voltage 650 V V_{DSS} Gate-Source Voltage-Continuous V V_{GS} ± 30 **Drain Current-Continuous** 7.8 А I_D Drain Current-Single Plused 31.2 А **I**DM Total Dissipation @Tc=25°C \mathbf{P}_{D} 80 W Max. Operating Junction Temperature 150 °C Τį Storage Temperature -55~150 °C Tstq

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.56	°C/W





isc website: <u>www.iscsemi.com</u>

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• ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 10mA	650			V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.3A	2.5		3.5	V
Vsd	Diode Forward On-voltage	I _S = 7.8A ;V _{GS} = 0			1.7	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =3.9A			0.67	Ω
lgss	Gate-Body Leakage Current	V _{GS} =±30V;V _{DS} =0			±1	μA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V; V _{GS} = 0			10	μA

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